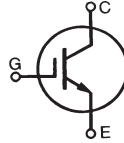


## GenX3™ 600V IGBT

**IXGA48N60A3**  
**IXGH48N60A3**  
**IXGP48N60A3**

Ultra Low V<sub>sat</sub> PT IGBT for  
up to 5kHz switching

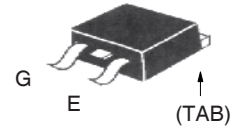


Symbol	Test Conditions	Maximum Ratings	
V <sub>CES</sub>	T <sub>C</sub> = 25°C to 150°C	600	V
V <sub>CGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GE</sub> = 1MΩ	600	V
V <sub>GES</sub>	Continuous	± 20	V
V <sub>GEM</sub>	Transient	± 30	V
I <sub>C110</sub>	T <sub>C</sub> = 110°C	48	A
I <sub>CM</sub>	T <sub>C</sub> = 25°C, 1ms	300	A
<b>SSOA</b> <b>(RBSOA)</b>	V <sub>GE</sub> = 15V, T <sub>VJ</sub> = 125°C, R <sub>G</sub> = 5Ω Clamped inductive load @ ≤ 600V	I <sub>CM</sub> = 96	A
P <sub>C</sub>	T <sub>C</sub> = 25°C	300	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6mm (0.062 in.) from case for 10s	300	°C
T <sub>SOLD</sub>	Plastic body for 10 seconds	260	°C
M <sub>d</sub>	Mounting torque (TO-247 & TO-220)	1.13/10	Nm/lb.in.
<b>Weight</b>	TO-247	6.0	g
	TO-220	3.0	g
	TO-263	2.5	g

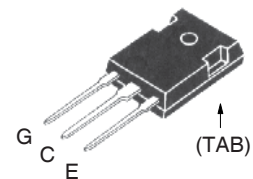
Symbol	Test Conditions (T <sub>J</sub> = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>CES</sub>	I <sub>C</sub> = 250μA, V <sub>GE</sub> = 0V	600		V
V <sub>GE(th)</sub>	I <sub>C</sub> = 250μA, V <sub>CE</sub> = V <sub>GE</sub>	3.0		5.0 V
I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub>			25 μA
	V <sub>GE</sub> = 0V, T <sub>J</sub> = 125°C			250 μA
I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ± 20V			±100 nA
V <sub>CE(sat)</sub>	I <sub>C</sub> = 32A, V <sub>GE</sub> = 15V, Note 1	1.18	1.35	V

**V<sub>CES</sub> = 600V**  
**I<sub>C110</sub> = 48A**  
**V<sub>CE(sat)</sub> ≤ 1.35V**

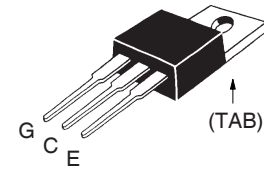
### TO-263 (IXGA)



### TO-247 (IXGH)



### TO-220 (IXGP)



G = Gate      C = Collector  
E = Emitter    TAB = Collector

### Features

- Optimized for low conduction losses
- International standard packages

### Advantages

- High power density
- Low gate drive requirement

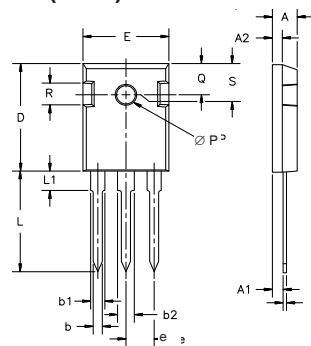
### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 32A, V_{CE} = 10V$ , Note 1	30	48	S
$C_{ies}$	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		3190	pF
$C_{oes}$			175	pF
$C_{res}$			43	pF
$Q_g$	$I_C = 32A, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		110	nC
$Q_{ge}$			21	nC
$Q_{gc}$			42	nC
$t_{d(on)}$	<b>Inductive Load, <math>T_J = 25^\circ C</math></b> $I_C = 32A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 5\Omega$		25	ns
$t_{ri}$			30	ns
$E_{on}$			0.95	mJ
$t_{d(off)}$			334	ns
$t_{fi}$			224	ns
$E_{off}$			2.90	mJ
$t_{d(on)}$	<b>Inductive Load, <math>T_J = 25^\circ C</math></b> $I_C = 32A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 5\Omega$		24	ns
$t_{ri}$			30	ns
$E_{on}$			1.97	mJ
$t_{d(off)}$			545	ns
$t_{fi}$			380	ns
$E_{off}$			5.60	mJ
$R_{thJC}$			0.42	$^\circ C/W$
$R_{thCS}$	(TO-247)	0.25		$^\circ C/W$
	(TO-220)	0.50		$^\circ C/W$

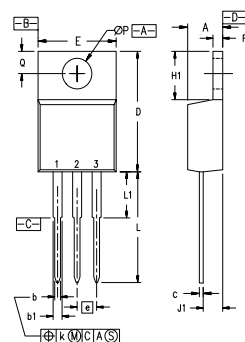
Note 1: Pulse test,  $t \leq 300\mu s$ ; duty cycle,  $d \leq 2\%$ .

### TO-247 (IXGH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

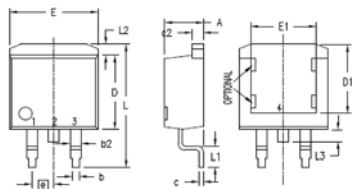
### TO-220 (IXGP) Outline



Pins: 1 - Gate 2 - Drain  
3 - Source 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

### TO-263 (IXGA) Outline



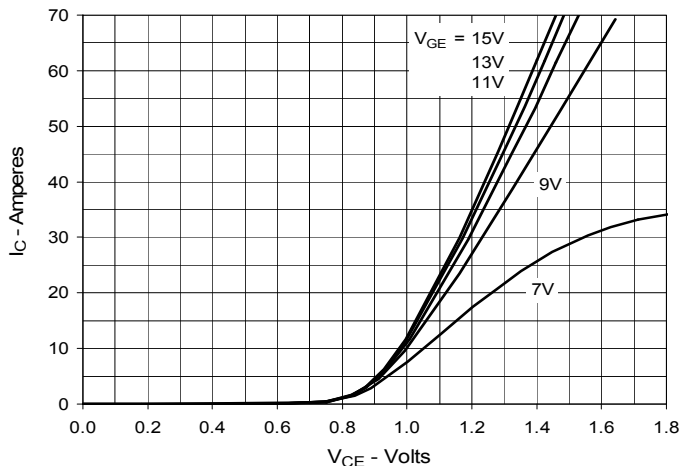
1. GATE (COLLECTOR)
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR) BOTTOM SIDE

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

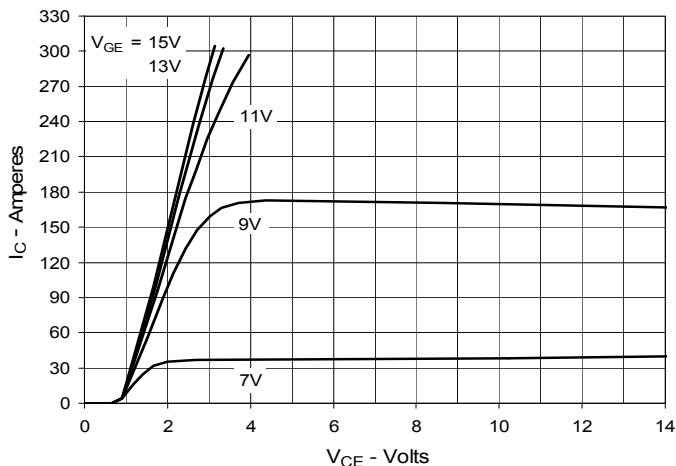
IXYS reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2  
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

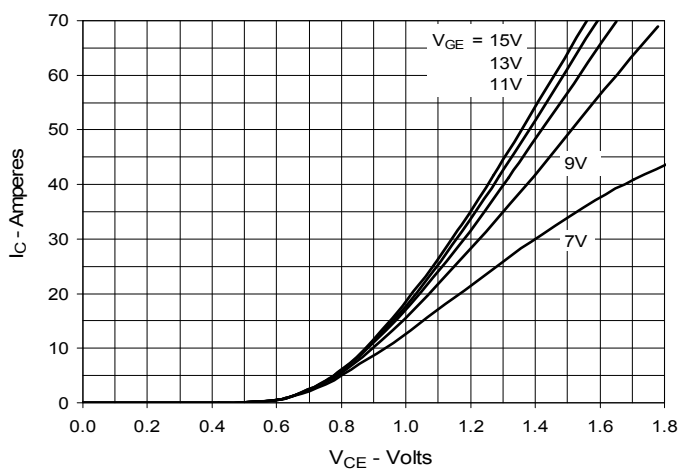
**Fig. 1. Output Characteristics @ 25°C**



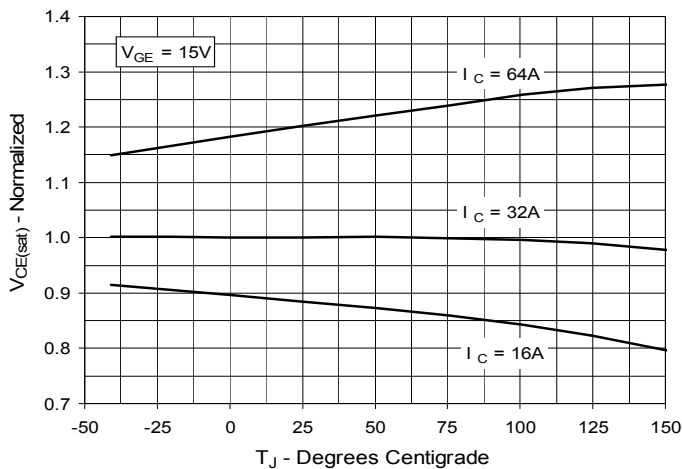
**Fig. 2. Extended Output Characteristics @ 25°C**



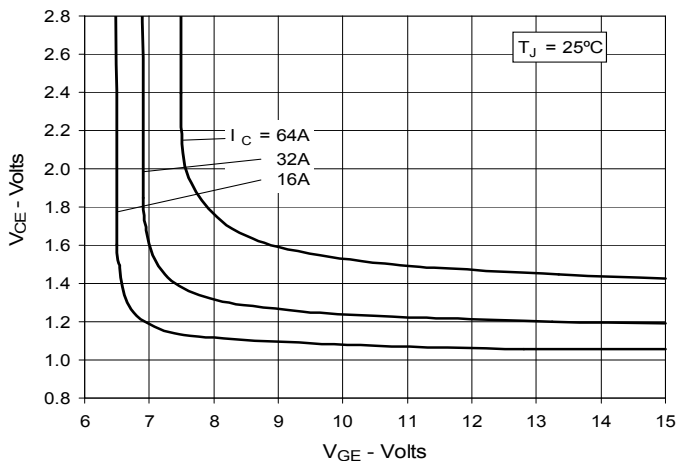
**Fig. 3. Output Characteristics @ 125°C**



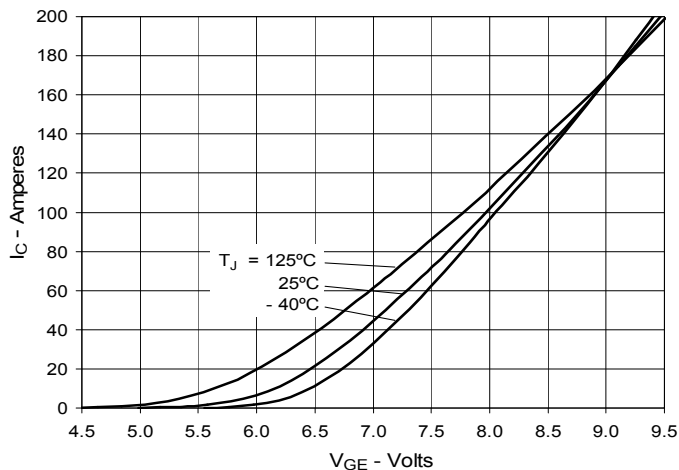
**Fig. 4. Dependence of VCE(sat) on Junction Temperature**



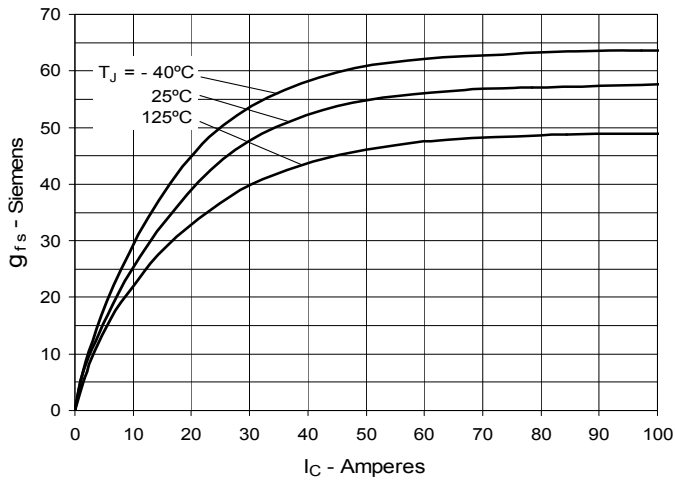
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



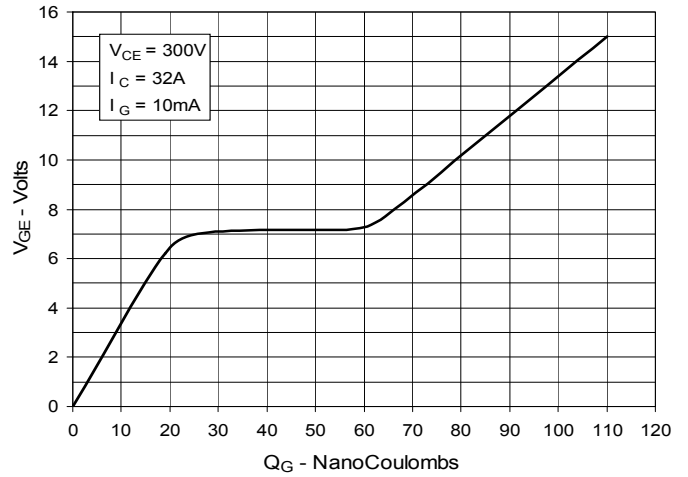
**Fig. 6. Input Admittance**



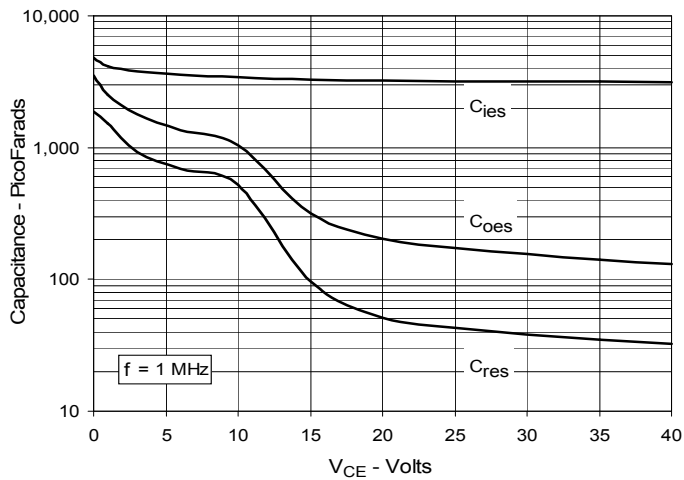
**Fig. 7. Transconductance**



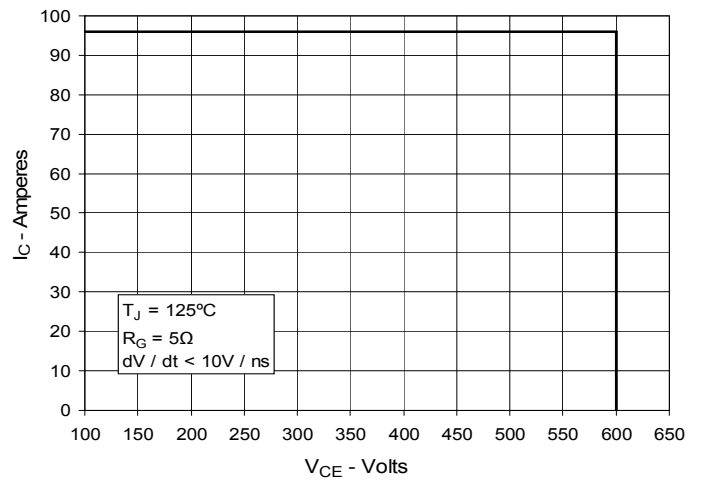
**Fig. 8. Gate Charge**



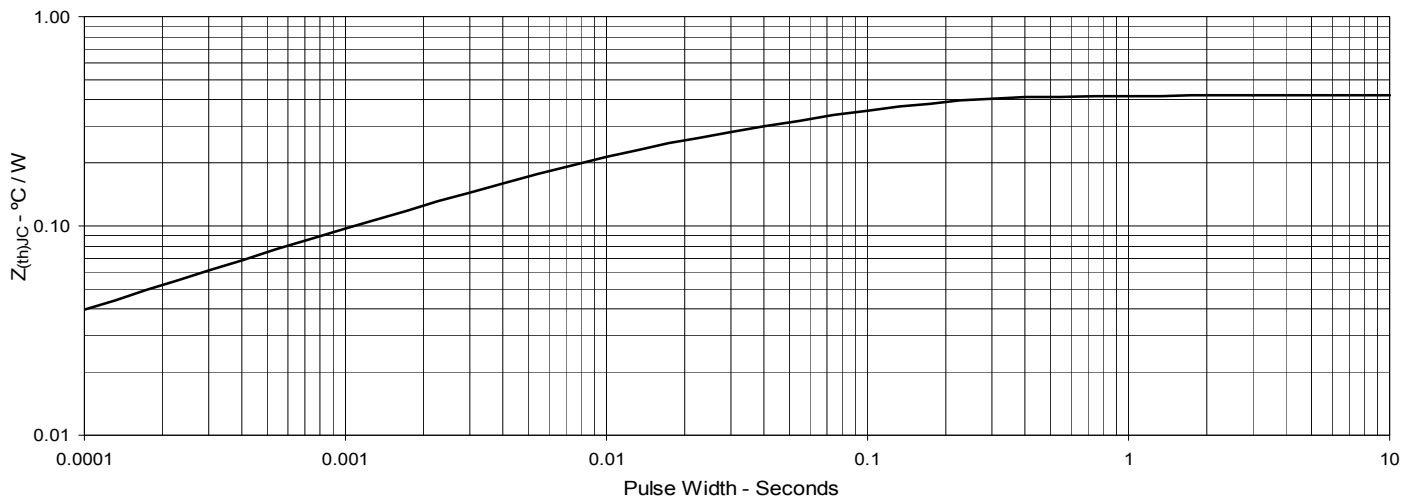
**Fig. 9. Capacitance**



**Fig. 10. Reverse-Bias Safe Operating Area**

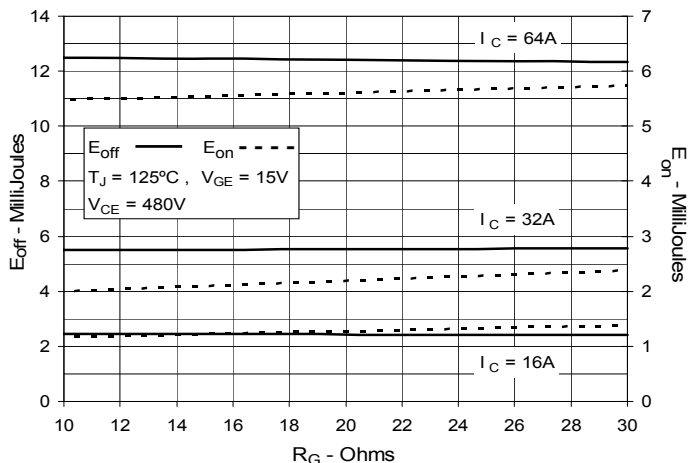


**Fig. 11. Maximum Transient Thermal Impedance**

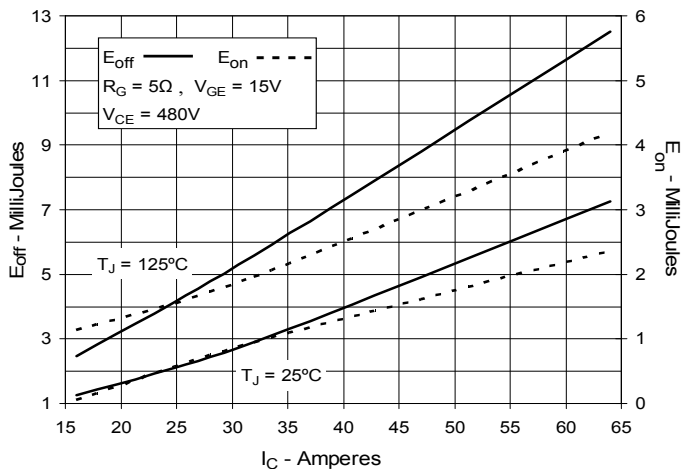


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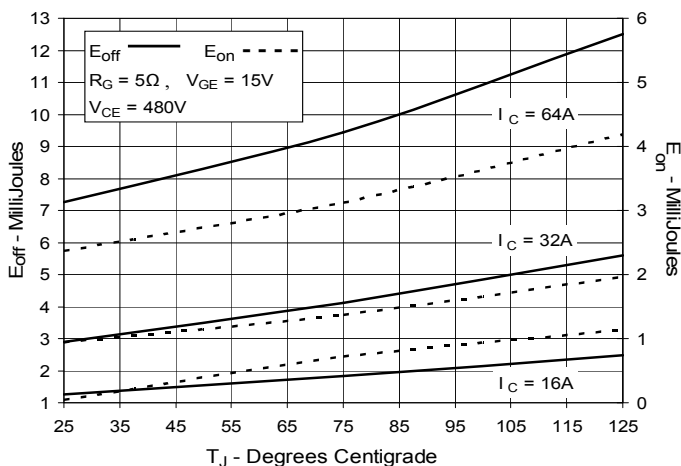
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



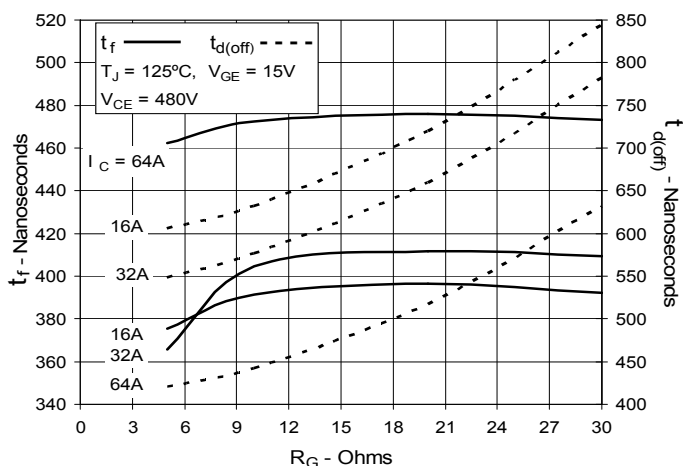
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



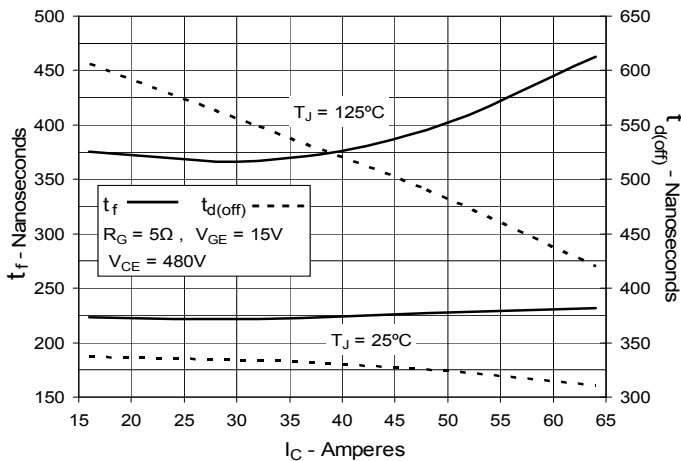
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



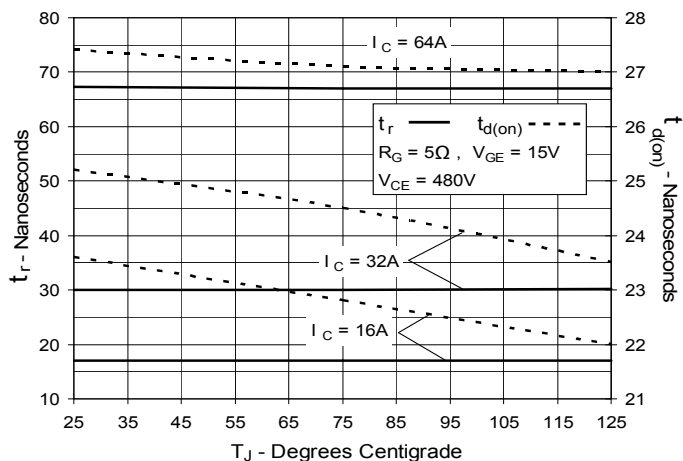
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



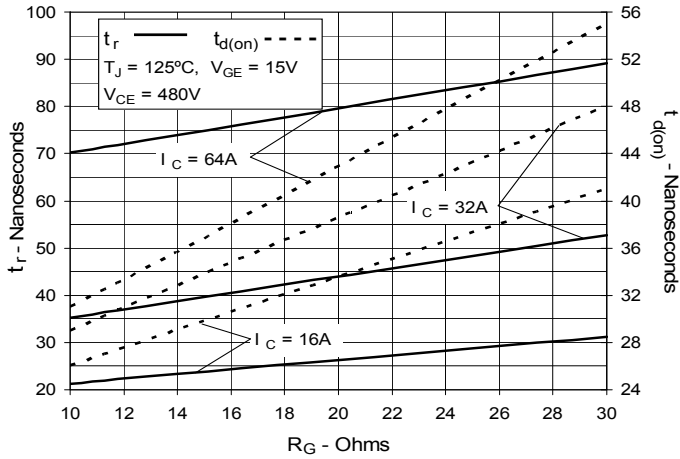
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



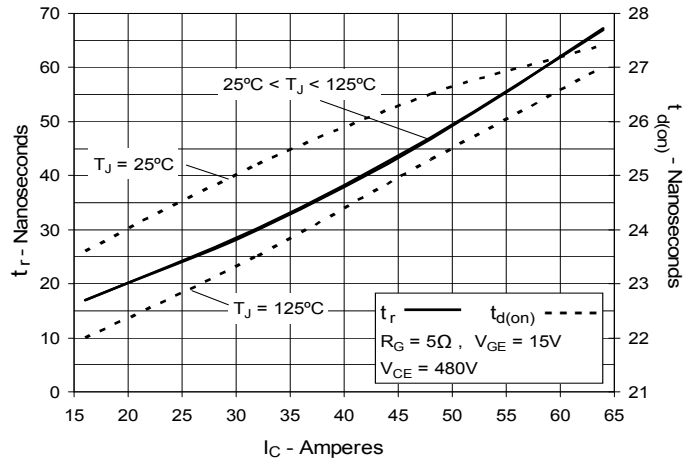
**Fig. 17. Inductive Turn-on Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-off Switching Times vs. Junction Temperature**

